LM119QML High Speed Dual Comparator

PDF.Support



Literature Number: SNOSAN3A

100 krad(Si)

100 krad(Si)

M119QML High Speed Dual Comparator



LM119QML **High Speed Dual Comparator**

General Description

The LM119 is a precision high speed dual comparator fabricated on a single monolithic chip. It is designed to operate over a wide range of supply voltages down to a single 5V logic supply and ground. Further, it has higher gain and lower input currents than devices like the LM710. The uncommitted collector of the output stage makes the LM119 compatible with RTL, DTL and TTL as well as capable of driving lamps and relavs at currents up to 25 mA.

Although designed primarily for applications requiring operation from digital logic supplies, the LM119 is fully specified for power supplies up to $\pm 15V$. It features faster response than the LM111 at the expense of higher power dissipation. However, the high speed, wide operating voltage range and low package count make the LM119 much more versatile than older devices like the LM711.

Features

- Available with radiation guaranteed — High Dose Rate – ELDRS Free
 - Two independent comparators
- Operates from a single 5V supply
- Typically 80 ns response time at ±15V
- Minimum fan-out of 2 each side
- Maximum input current of 1 µA over temperature
- Inputs and outputs can be isolated from system ground -
- High common mode slew rate

NS Part Number	SMD Part Number	NS Package Number	Package Description
LM119E/883		E20A	20LD LCC
LM119E-SMD	86014012A	E20A	20LD LCC
LM119H/883		H10C	10LD T0-100 Metal Can
LM119H-SMD	8601401IA	H10C	10LD T0-100 Metal Can
LM119H-QMLV	5962-9679801VIA	H10C	10LD T0-100 Metal Can
LM119HRQMLV	5962R9679801VIA	H10C	10LD T0-100 Metal Can
HIGH DOSE RATE (Note 13)	100 krad(Si)		
LM119HRLQMLV	5962R9679802VIA	H10C	10LD T0-100 Metal Can
ELDRS FREE (Note 14)	100 krad(Si)		
LM119J/883		J14A	14LD CERDIP
LM119J-SMD	8601401CA	J14A	14LD CERDIP
LM119J-QMLV	5962-9679801VCA	J14A	14LD CERDIP
LM119JRQMLV	5962R9679801VCA	J14A	14LD CERDIP
HIGH DOSE RATE (Note 13)	100 krad(Si)		
LM119JRLQMLV	5962R9679802VCA	J14A	14LD CERDIP
ELDRS FREE (Note 14)	100 krad(Si)		
LM119W/883		W10A	10LD CERPAK
LM119W-SMD	8601401HA	W10A	10LD CERPAK
LM119W-QMLV	5962-9679801VHA	W10A	10LD CERPAK
LM119WRQMLV	5962R9679801VHA	W10A	10LD CERPAK
HIGH DOSE RATE (Note 13)	100 krad(Si)		
LM119WRLQMLV	5962R9679802VHA	W10A	10LD CERPAK
ELDRS FREE (Note 14)	100 krad(Si)		
LM119WG/883		WG10A	10LD Ceramic SOIC
LM119WG-QMLV	5962-9679801VXA	WG10A	10LD Ceramic SOIC
LM119WGRQMLV	5962R9679801VXA	WG10A	10LD Ceramic SOIC
HIGH DOSE RATE (Note 14)	100 krad(Si)		

Ordering Information

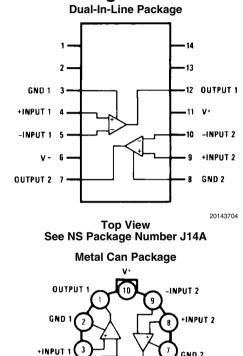
NS Part Number	SMD Part Number	NS Package Number	Package Description
LM119WGRLQMLV	5962R9679802VXA	WG10A	10LD Ceramic SOIC
ELDRS FREE (Note 14)	100 krad(Si)		
LM119 MDE	5962R9679802V9A		
ELDRS FREE DIE	100 krad(Si)		
(Notes 1, 14)			
LM119 MDR	5962R9679801V9A		
HIGH DOSE RATE DIE	100 krad(Si)		
(Notes 1, 13)			

Note 1: FOR ADDITIONAL DIE INFORMATION, PLEASE VISIT THE HI REL WEB SITE AT: www.national.com/analog/space/level_die

Connection Diagrams

-INPUT 1

Case is connected to pin 5 (V-)

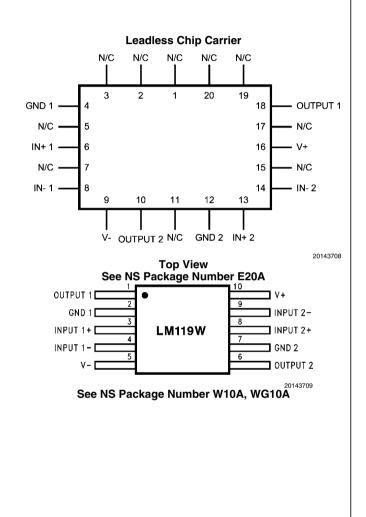


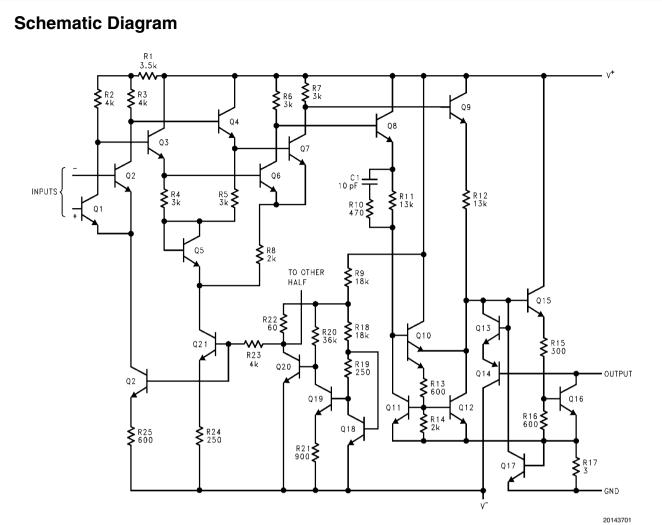
Top View See NS Package Number H10C

GND 2

20143707

OUTPUT 2





*Do not operate the LM119 with more than 16V between GND and V+

Absolute Maximum Ratings (Note 2)

Total Supply Voltage	36V
Output to Negative Supply Voltage	36V
Ground to Negative Supply Voltage	25V
Ground to Positive Supply Voltage	18V
Differential Input Voltage	±5V
Input Voltage (Note 4)	±15V
Power Dissipation (Note 3)	500 mW
Output Short Circuit Duration	10 sec
Storage Temperature Range	–65°C ≤ T _A ≤ 150°C
Operating Ambient Temperature Range	–55°C ≤ T _A ≤ 125°C
Maximum Junction Temperature (T _{.1})	150°C
Lead Temperature (Soldering, 10 sec.)	260°C
Thermal Resistance	
θ _{JA}	
E Package (Still Air)	89°C/W
E Package (500LF/Min Air flow)	63°C/W
H Package (Still Air)	162°C/W
H Package (500LF/Min Air flow)	88°C/W
J Package (Still Air)	94°C/W
J Package (500LF/Min Air flow)	52°C/W
W Package (Still Air)	215°C/W
W Package (500LF/Min Air flow)	132°C/W
WG Package (Still Air)	215°C/W
WG Package (500LF/Min Air flow)	132°C/W
θ _{JC}	
E Package	5°C/W
H Package	31°C/W
J Package	11°C/W
W Package	13°C/W
WG Package	13°C/W
Package Weight	
E Package	TBD
H Package	TBD
J Package	TBD
W Package	TBD
WG Package	225mg
ESD rating (Note 5)	800V

Quality Conformance Inspection Mil-Std-883, Method 5005 - Group A

Subgroup	Description	Temp °C
1	Static tests at	25
2	Static tests at	125
3	Static tests at	-55
4	Dynamic tests at	25
5	Dynamic tests at	125
6	Dynamic tests at	-55
7	Functional tests at	25
8A	Functional tests at	125
8B	Functional tests at	-55
9	Switching tests at	25
10	Switching tests at	125
11	Switching tests at	-55
12	Settling time at	25
13	Settling time at	125
14	Settling time at	-55

LM119/883 Electrical Characteristics

DC Parameters

The following conditions apply, unless otherwise specified. $~~V_{CM}$ = 0V ~~

Symbol	Parameter	Conditions	Notes	Min	Max	Units	Sub- groups
+I _{CC}	Positive Supply Current	$\pm V_{CC} = \pm 15V, V_O = Low$			11	mA	1
		$V^+ = 5.6V$ thru $1.4K\Omega$			11.5	mA	2
-I _{cc}	Negative Supply Current	$\pm V_{CC} = \pm 15V, V_{O} = Low$		-4.2		mA	1
		$V^+ = 5.6V$ thru $1.4K\Omega$		-4.5		mA	2
Leak	Output Leakage Current	$+V_{CC} = 15V, -V_{CC} = -1V,$			1.8	μA	1
		$V_{Gnd} = 0V, V_O = 35V,$			9.5	μA	2
		$V_1 = 5mV$			10.0	μA	3
IB	Input Bias Current	$\pm V_{CC} = \pm 15V$			0.475	μA	1
					0.95	μA	2, 3
		$^{+}V_{CC} = 5V, -V_{CC} = 0V,$			0.475	μA	1
		$V_{CM} = 1.5V$.95	μA	2, 3
V _{IO}	Input Offset Voltage	$+V_{CC} = 5V, -V_{CC} = 0V,$		-3.8	3.8	mV	1
		V _{CM} = 1V, R _S ≤ 5KΩ		-6.8	6.8	mV	2, 3
		$+V_{CC} = 5V, -V_{CC} = 0V,$		-3.8	3.8	mV	1
		$V_{CM} = 3V, R_S \le 5K\Omega$		-6.8	6.8	mV	2, 3
		$\pm V_{CC} = \pm 15V, V_{CM} = 12V,$		-3.8	3.8	mV	1
		$R_{\rm S} \le 5K\Omega$		-6.8	6.8	mV	2, 3
		$\pm V_{CC} = \pm 15V, V_{CM} = -12V,$		-3.8	3.8	mV	1
		R _s ≤ 5KΩ		-6.8	6.8	mV	2, 3
10	Input Offset Current	$+V_{CC} = 5V, -V_{CC} = 0V, V_{CM} = 1V$		-75	75	nA	1
10		$\mathcal{C}\mathcal{C} = \mathcal{C}\mathcal{C}$, $\mathcal{C}\mathcal{C} = \mathcal{C}\mathcal{C}$, $\mathcal{C}\mathcal{M} = \mathcal{C}\mathcal{C}$		-100	100	nA	2, 3
		$+V_{CC} = 5V, -V_{CC} = 0V, V_{CM} = 3V$		-75	75	nA	1
				-100	100	nA	2, 3
		$\pm V_{CC} = \pm 15V, V_{CM} = 12V$		-75	75	nA	1
				-100	100	nA	2, 3
		$\pm V_{CC} = \pm 15V, V_{CM} = -12V$		-75	75	nA	1
				-100	100	nA	2, 3
V _{Sat}	Output Saturation Voltage	$\pm V_{CC} = \pm 15V$, $I_0 = 25mA$, $V_1 = -5mV$			1.5	V	1
		$+V_{CC} = 5V, -V_{CC} = 0V,$	(Note 12)		0.4	V	1, 2
		I _O = 4.0mA	(Note 12)		0.6	V	3
A _V	Voltage Gain	$\pm V_{CC} = \pm 15V$, Delta V _O = 12V,	(Note 9),	10.5		K	4
·		$R_{L} = 1.4 K\Omega$	(Note 10)				
			(Note 9), (Note 10)	10		К	5, 6
		$^+V_{CC} = 5V, -V_{CC} = 0V,$ Delta V _O = 4.5V, R _L = 1.4KΩ	(Note 9), (Note 11)	8.0		К	4
			(Note 9), (Note 11)	5.0		К	5
			(Note 9), (Note 11)	5.8		К	6

LM119-SMD Electrical Characteristics

SMD 8601401

DC Parameters

The following conditions apply, unless otherwise specified. $\ V_{CM}=0V$

Symbol	Parameter	Conditions	Notes	Min	Max	Units	Sub- groups
+I _{CC}	Positive Supply Current	$\pm V_{CC} = \pm 15V, V_{O} = Low$			11	mA	1
		$V^+ = 5.6V$ thru $1.4K\Omega$			11.5	mA	2, 3
-I _{cc}	Negative Supply Current	$\pm V_{CC} = \pm 15V, V_{O} = Low$		-4.2		mA	1
		$V^+ = 5.6V$ thru 1.4K Ω		-4.5		mA	2
				-6.0		mA	3
I _{Leak}	Output Leakage Current	$^{+}V_{CC} = 15V, ^{-}V_{CC} = -1V,$	(Note 6)		1.8	μA	1
		$V_{Gnd} = 0V, V_O = 35V$	(Note 6)		10	μA	2, 3
I _{IB}	Input Bias Current	$\pm V_{CC} = \pm 15V$			0.475	μA	1
					0.95	μA	2, 3
		$^{+}V_{CC} = 5V$	(Note 7)		0.475	μA	1
			(Note 7)		.95	μA	2, 3
V _{IO}	Input Offset Voltage	$+V_{CC} = 5V, V_{CM} = 1V, R_S \le 5K\Omega$	(Note 7)	-3.8	3.8	mV	1
			(Note 7)	-6.8	6.8	mV	2, 3
		$+V_{CC} = 5V, V_{CM} = 3V,$	(Note 7)	-3.8	3.8	mV	1
		$R_{S} \leq 5K\Omega$	(Note 7)	-6.8	6.8	mV	2, 3
		$\pm V_{CC} = \pm 15V, V_{CM} = 12V,$		-3.8	3.8	mV	1
		R _s ≤ 5KΩ		-6.8	6.8	mV	2, 3
		$\pm V_{CC} = \pm 15V, V_{CM} = -12V,$		-3.8	3.8	mV	1
		R _s ≤ 5KΩ		-6.8	6.8	mV	2, 3
I _{IO}	Input Offset Current	$+V_{CC} = 5V, V_{CM} = 1V$	(Note 7)	-75	75	nA	1
			(Note 7)	-100	100	nA	2, 3
		$+V_{CC} = 5V, V_{CM} = 3V$	(Note 7)	-75	75	nA	1
			(Note 7)	-100	100	nA	2, 3
		$\pm V_{CC} = \pm 15V, V_{CM} = 12V$		-75	75	nA	1
				-100	100	nA	2, 3
		$\pm V_{CC} = \pm 15V, V_{CM} = -12V$		-75	75	nA	1
				-100	100	nA	2, 3
VI	Input Voltage Range	+V _{CC} = 5V	(Note 7), (Note 8)	1.0	3.0	V	1, 2, 3
		$\pm V_{CC} = \pm 15V$	(Note 8)	-12	12	V	1, 2, 3
V _{Sat}	Output Saturation Voltage	$\pm V_{CC} = \pm 15V$, $I_0 = 25mA$, $V_1 \leq -5mV$	(Note 6)		1.5	V	1, 2, 3
		+V _{CC} = 3.5V, -V _{CC} = -1V,			0.4	V	1, 2
		$V_1 \leq -6mV, I_0 \leq 3.2mA$			0.6	V	3
A _V	Voltage Gain	$\pm V_{CC} = \pm 15V$, Delta $V_{O} = 12V$,	(Note 9)	10.5		К	4
v		$R_L = 1.4K\Omega$	(Note 9)	10		K	5, 6
		$^{+}V_{CC} = 5V, ^{-}V_{CC} = 0V,$ Delta V _Ω = 4.5V, R ₁ = 1.4KΩ	(Note 7), (Note 9)	8.0		K	4
		Dena $v_0 = 4.5v, n_1 = 1.4n_{52}$	(Note 9) (Note 7), (Note 9)	5.0		К	5
			(Note 7), (Note 9)	5.8		К	6
CMRR	Common Mode Rejection Ratio	$\pm V_{CC} = \pm 15V, V_{CM} = \pm 12V$	· · · · /	80		dB	4

LM119 Electrical Characteristics SMD 5962-9679801, HIGH DOSE RATE DC Parameters

The following conditions apply, unless otherwise specified. $V_{CM} = 0V$

Symbol	Parameter	Conditions	Notes	Min	Max	Units	Sub- groups
+I _{CC}	Positive Supply Current	$\pm V_{CC} = \pm 15V, V_{O} = Low$			11	mA	1
		V+ = 5.6V thru 1.4KΩ			11.5	mA	2, 3
-I _{CC}	Negative Supply Current	$\pm V_{CC} = \pm 15V, V_{O} = Low$		-4.2		mA	1
		V+ = 5.6V thru 1.4KΩ		-4.5		mA	2
				-6.0		mA	3
l _{Leak}	Output Leakage Current	$^{+}V_{CC} = 15V, ^{-}V_{CC} = -1V,$	(Note 6)		1.8	μΑ	1
		$V_{Gnd} = 0V, V_O = 35V$	(Note 6)		10	μA	2, 3
IB	Input Bias Current	$\pm V_{CC} = \pm 15V$			0.475	μA	1
					0.95	μΑ	2, 3
		$^{+}V_{CC} = 5V$	(Note 7)		0.475	μA	1
			(Note 7)		.95	μΑ	2, 3
V _{IO}	Input Offset Voltage	$^+V_{CC} = 5V, V_{CM} = 1V, R_S \le 5K\Omega$	(Note 7)	-3.8	3.8	mV	1
			(Note 7)	-6.8	6.8	mV	2, 3
		$^{+}V_{CC} = 5V, V_{CM} = 3V,$	(Note 7)	-3.8	3.8	mV	1
		R _S ≤ 5KΩ	(Note 7)	-6.8	6.8	mV	2, 3
		$\pm V_{CC} = \pm 15V, V_{CM} = 12V,$		-3.8	3.8	mV	1
		R _S ≤5KΩ		-6.8	6.8	mV	2, 3
		$\pm V_{CC} = \pm 15V, V_{CM} = -12V,$		-3.8	3.8	mV	1
		R _S ≤ 5KΩ		-6.8	6.8	mV	2, 3
I _{IO}	Input Offset Current	$^{+}V_{CC} = 5V, V_{CM} = 1V$	(Note 7)	-75	75	nA	1
			(Note 7)	-100	100	nA	2, 3
		$+V_{CC} = 5V, V_{CM} = 3V$	(Note 7)	-75	75	nA	1
			(Note 7)	-100	100	nA	2, 3
		$\pm V_{CC} = \pm 15V, V_{CM} = 12V$		-75	75	nA	1
				-100	100	nA	2, 3
		$\pm V_{CC} = \pm 15V, V_{CM} = -12V$		-75	75	nA	1
			(Niete 7)	-100	100	nA V	2, 3
VI	Input Voltage Range	$^{+}V_{CC} = 5V$	(Note 7), (Note 8)	1.0	3.0	v	1, 2, 3
		$\pm V_{CC} = \pm 15V$	(Note 8)	-12	12	V	1, 2, 3
V _{Sat}	Output Saturation Voltage	$\pm V_{CC} = \pm 15V, I_{O} = 25mA,$	(Note 6)		1.5	V	1, 2, 3
Jai		$ V_1 \leq -5mV$, ,				
		$^{+}V_{CC} = 3.5V, ^{-}V_{CC} = -1V,$			0.4	V	1, 2
		$V_1 \leq -6mV, I_0 \leq 3.2mA$			0.6	V	3
A _V	Voltage Gain	$\pm V_{CC} = \pm 15V$, Delta $V_{O} = 12V$,	(Note 9)	10.5		K	4
v		$R_{\rm L} = 1.4 \text{K}\Omega$	(Note 9)	10		ĸ	5, 6
		$+V_{CC} = 5V, -V_{CC} = 0V,$	(Note 7),	8.0		K	4
		Delta $V_{\Omega} = 4.5V$, $R_{L} = 1.4K\Omega$	(Note 9)				
			(Note 7),	5.0		К	5
			(Note 9)				
			(Note 7),	5.8		К	6
CMRR	Common Mode Rejection Ratio		(Note 9)	80		dB	4
	Common Mode Rejection Ratio	$\pm V_{CC} = \pm 15V, V_{CM} = \pm 12V$		00		uБ	4

SMD 5962-9679801, HIGH DOSE RATE DC DELTA Parameters

The following conditions apply, unless otherwise specified.

 $V_{CM} = 0V$, Delta calculations performed on QMLV devices at group B, subgroup 5 only.

Symbol	Parameter	Conditions	Notes	Min	Max	Units	Sub- groups
+I _{CC}	Positive Supply Current	$\pm V_{CC} = \pm 15V, V_{O} = Low$		-1.0	1.0	mA	1
		$V^+ = 5.6V$ thru $1.4K\Omega$					
-I _{CC}	Negative Supply Current	$\pm V_{CC} = \pm 15V, V_{O} = Low$		-0.5	0.5	mA	1
		$V^+ = 5.6V$ thru $1.4K\Omega$					
V _{IO}	Input Offset Voltage	$^+V_{CC} = 5V, V_{CM} = 1V, R_S \le 5K\Omega$		-0.4	0.4	mV	1

SMD 5962-9679801, High Dose Rate 100K Post Radiation Parameters @ 25°C

100K Post Radiation Parameters @ 25^{\circ}C (Note 13) The following conditions apply, unless otherwise specified. $V_{CM} = 0V$

Symbol	Parameter	Conditions	Notes	Min	Мах	Units	Sub- groups
I _{IB}	Input Bias Current	$\pm V_{CC} = \pm 15V$			1.0	μA	1
		$V_{CC} = 5V$			1.0	μA	1
V _{IO}	Input Offset Voltage	$^+V_{CC} = 5V, V_{CM} = 1V, R_S \le 5K\Omega$		-4.0	4.0	mV	1
		$^+V_{CC} = 5V, V_{CM} = 3V, R_S \le 5K\Omega$		-4.0	4.0	mV	1
		$\pm V_{CC} = \pm 15V, V_{CM} = 12V, R_S \leq$		-4.0	4.0	mV	1
		$5K\Omega$ ±V _{CC} = ±15V, V _{CM} = -12V, R _S ≤		-4.0	4.0	mV	1
		5ΚΩ					

LM119 Electrical Characteristics SMD 5962-9679802, ELDRS FREE DC Parameters

The following conditions apply, unless otherwise specified. $V_{CM} = 0V$

Symbol	Parameter	Conditions	Notes	Min	Мах	Units	Sub- groups
+I _{CC}	Positive Supply Current	$\pm V_{CC} = \pm 15V, V_{O} = Low$			11	mA	1
		V+ = 5.6V thru 1.4KΩ			11.5	mA	2, 3
-I _{cc}	Negative Supply Current	$\pm V_{CC} = \pm 15V, V_{O} = Low$		-4.2		mA	1
		V+ = 5.6V thru 1.4KΩ		-4.5		mA	2
				-6.0		mA	3
Leak	Output Leakage Current	$^{+}V_{CC} = 15V, ^{-}V_{CC} = -1V,$	(Note 6)		1.8	μA	1
		$V_{Gnd} = 0V, V_{O} = 35V$	(Note 6)		10	μA	2, 3
I _{IB}	Input Bias Current	$\pm V_{CC} = \pm 15V$			0.475	μA	1
					0.95	μA	2, 3
		$+V_{CC} = 5V$	(Note 7)		0.475	μA	1
			(Note 7)		.95	μA	2, 3
V _{IO}	Input Offset Voltage	$+V_{CC} = 5V, V_{CM} = 1V, R_S \le 5K\Omega$	(Note 7)	-3.8	3.8	mV	1
			(Note 7)	-6.8	6.8	mV	2, 3
		$+V_{CC} = 5V, V_{CM} = 3V,$	(Note 7)	-3.8	3.8	mV	1
		R _S ≤ 5KΩ	(Note 7)	-6.8	6.8	mV	2, 3
		$\pm V_{CC} = \pm 15V, V_{CM} = 12V,$		-3.8	3.8	mV	1
		R _s ≤ 5KΩ		-6.8	6.8	mV	2, 3
		$\pm V_{CC} = \pm 15V, V_{CM} = -12V,$		-3.8	3.8	mV	1
		R _s ≤ 5KΩ		-6.8	6.8	mV	2, 3
10	Input Offset Current	$+V_{CC} = 5V, V_{CM} = 1V$	(Note 7)	-75	75	nA	1
			(Note 7)	-100	100	nA	2, 3
		$+V_{CC} = 5V, V_{CM} = 3V$	(Note 7)	-75	75	nA	1
			(Note 7)	-100	100	nA	2, 3
		$\pm V_{CC} = \pm 15V, V_{CM} = 12V$		-75	75	nA	1
				-100	100	nA	2, 3
		$\pm V_{CC} = \pm 15V, V_{CM} = -12V$		-75	75	nA	1
				-100	100	nA	2, 3
VI	Input Voltage Range	+V _{CC} = 5V	(Note 8), (Note 8)	1.0	3.0	V	1, 2, 3
		$\pm V_{CC} = \pm 15V$	(Note 8)	-12	12	V	1, 2, 3
V _{Sat}	Output Saturation Voltage	$\pm V_{CC} = \pm 15V, I_{O} = 25mA,$	(Note 6)		1.5	V	1, 2, 3
our		$V_{\rm I} \leq -5 {\rm mV}$					
		$^{+}V_{CC} = 3.5V, ^{-}V_{CC} = -1V,$			0.4	V	1, 2
		$V_1 \leq -6mV$, $I_0 \leq 3.2mA$			0.6	V	3
A _V	Voltage Gain	$\pm V_{CC} = \pm 15V$, Delta $V_{O} = 12V$,	(Note 9)	10.5		K	4
v		$R_L = 1.4K\Omega$	(Note 9)	10		K	5, 6
		$+V_{CC} = 5V, -V_{CC} = 0V,$	(Note 7),	8.0		K	4
		Delta V _O = 4.5V, R _L = 1.4K Ω	(Note 9)				
			(Note 7),	5.0		К	5
			(Note 9) (Note 7),	5.8		K	6
CMRR	Common Mada Bajastian Batia	$\pm 1/2 = \pm 151/2/2 = \pm 101/2$	(Note 9)	00		DY	
	Common Mode Rejection Ratio	$\pm V_{CC} = \pm 15V, V_{CM} = \pm 12V$		80		dB	4

SMD 5962-9679802, ELDRS FREE DC DELTA Parameters

The following conditions apply, unless otherwise specified.

V_{CM} = 0V, Delta calculations performed on QMLV devices at group B, subgroup 5 only.

Symbol	Parameter	Conditions	Notes	Min	Max	Units	Sub- groups
+I _{CC}	Positive Supply Current	$\pm V_{CC} = \pm 15V, V_{O} = Low$		-1.0	1.0	mA	1
		$V^+ = 5.6V$ thru $1.4K\Omega$					
-I _{CC}	Negative Supply Current	$\pm V_{CC} = \pm 15V, V_{O} = Low$		-0.5	0.5	mA	1
		$V^+ = 5.6V$ thru $1.4K\Omega$					
V _{IO}	Input Offset Voltage	$^+V_{CC} = 5V, V_{CM} = 1V, R_S \le 5K\Omega$		-0.4	0.4	mV	1

SMD 5962-9679802, ELDRS FREE 100K Post Radiation Parameters @ 25°C (Note 14)

The following conditions apply, unless otherwise specified. $V_{CM} = 0V$

Symbol	Parameter	Conditions	Notes	Min	Max	Units	Sub- groups
I _{IB}	Input Bias Current	$\pm V_{CC} = \pm 15V$			1.0	μA	1
		$V_{\rm CC} = 5V$			1.0	μA	1
V _{IO}	Input Offset Voltage	$^+V_{CC} = 5V, V_{CM} = 1V, R_S \le 5K\Omega$		-4.0	4.0	mV	1
		$+V_{CC} = 5V, V_{CM} = 3V, R_S \le 5K\Omega$		-4.0	4.0	mV	1
		$\pm V_{CC} = \pm 15V, V_{CM} = 12V, R_S \le 5K\Omega$		-4.0	4.0	mV	1
		$\pm V_{CC} = \pm 15V, V_{CM} = -12V, R_S \le 5K\Omega$		-4.0	4.0	mV	1

Note 2: Absolute Maximum Ratings indicate limits beyond which damage to the device may occur. Operating Ratings indicate conditions for which the device is functional, but do not guarantee specific performance limits. For guaranteed specifications and test conditions, see the Electrical Characteristics. The guaranteed specifications apply only for the test conditions listed. Some performance characteristics may degrade when the device is not operated under the listed test conditions.

Note 3: The maximum power dissipation must be derated at elevated temperatures and is dictated by T_{Jmax} (maximum junction temperature), θ_{JA} (package junction to ambient thermal resistance), and T_A (ambient temperature). The maximum allowable power dissipation at any temperature is $P_{Dmax} = (T_{Jmax} - T_A)/\theta_{JA}$ or the number given in the Absolute Maximum Ratings, whichever is lower.

Note 4: For supply voltages less than ±15V the absolute maximum input voltage is equal to the supply voltage.

Note 5: Human Body model, $1.5K\Omega$ in series with 100pF.

Note 6: $V_I \ge 8mV$ at extremes for I_{Leak} and $V_I \le -8mV$ at extremes for V_{Sat} (V_I to exceed V_{OS} .

Note 7: 5V differential across $+V_{CC}$ and $-V_{CC}$.

Note 8: Parameter guaranteed by V_{IO} and I_{IO} tests.

Note 9: K = V/mV.

Note 10: Gain is computed with an output swing from +13.5V to +1.5V.

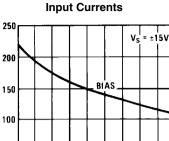
Note 11: Gain is computed with an output swing from +5.0V to +0.5V.

Note 12: Output is monitored by measuring V₁ with limits from 0 to 6mV at all temperatures

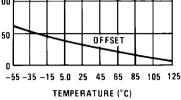
Note 13: Pre and post irradiation limits are identical to those listed under AC and DC electrical characteristics except as listed in the Post Radiation Limits Table. These parts may be dose rate sensitive in a space environment and demonstrate enhanced low dose rate sensitivity. Radiation end point limits for the noted parameters are guaranteed only for the conditions as specified in MIL-STD-883, per Test Method 1019, Condition A.

Note 14: Pre and post irradiation limits are identical to those listed under AC and DC electrical characteristics except as listed in the Post Radiation Limits Table. Low dose rate testing has been performed on a wafer-by-wafer basis, per Test Method 1019, Condition D of MIL-STD-883, with no enhanced low dose rate sensitivity (ELDRS).

Typical Performance Characteristics

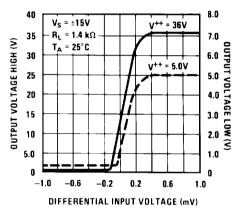


INPUT CURRENT (nA)

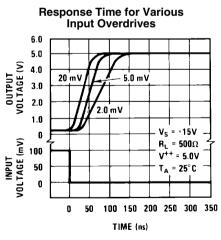




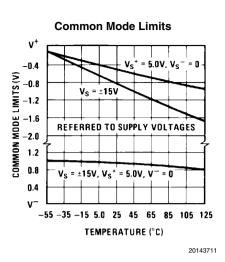


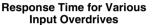


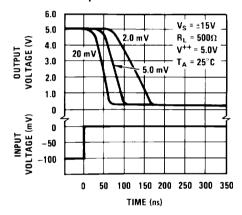
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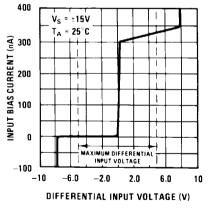




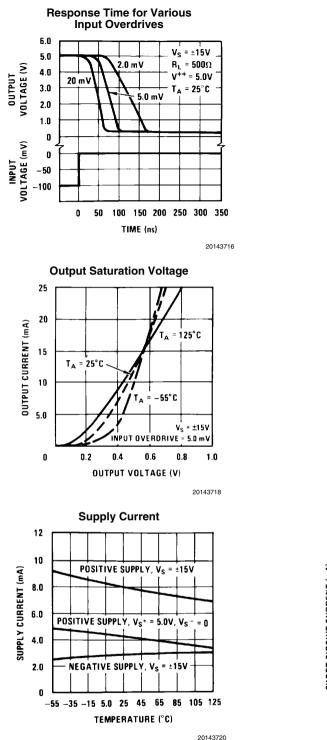


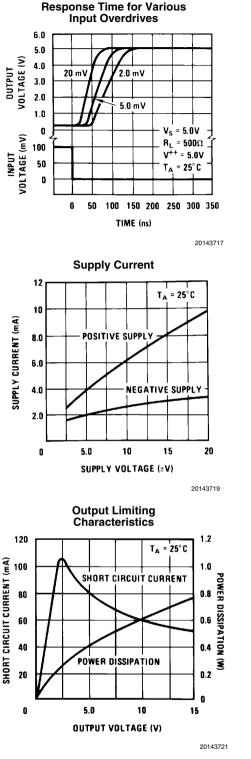
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Input Characteristics

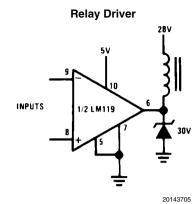


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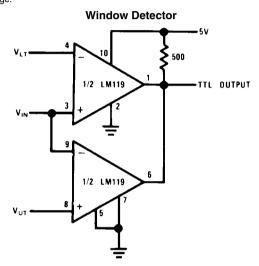




Typical Applications (Note Pin numbers are for metal can package.)



Note 15: Pin numbers are for metal can package.

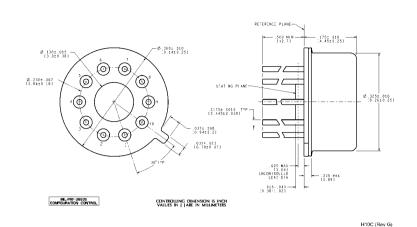


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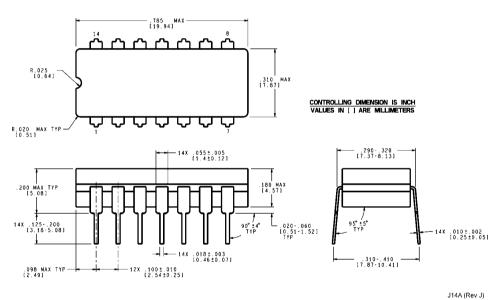
 $\begin{aligned} & V_{\text{OUT}} = 5 \text{V for } V_{\text{LT}} \leq V_{\text{IN}} \leq V_{\text{UT}} \\ & V_{\text{OUT}} = 0 \text{ for } V_{\text{IN}} \leq V_{\text{LT}} \text{or } V_{\text{IN}} \geq V_{\text{UT}} \end{aligned}$

Revision History							
Date Released	Revision	Section	Originator	Changes			
07/24/08	A	New release to corporate format	L. Lytle	2 MDS datasheets converted into one corporate data sheet format. Added Radiation information. MDS data sheets MNLM119-X Rev. 0F1 & MDLM119-X Rev 2A2 will be archived.			
01/13/09	В	Features, Ordering Info., Electrical Section, Notes 13 and 14	Larry McGee	Added reference to ELDRS and Die NSID's to data sheet. Correction from: 100k rd(Si) to 100 krad(Si) in ordering info. Changed wording in Notes 13 and 14 Revision A will be Archived.			

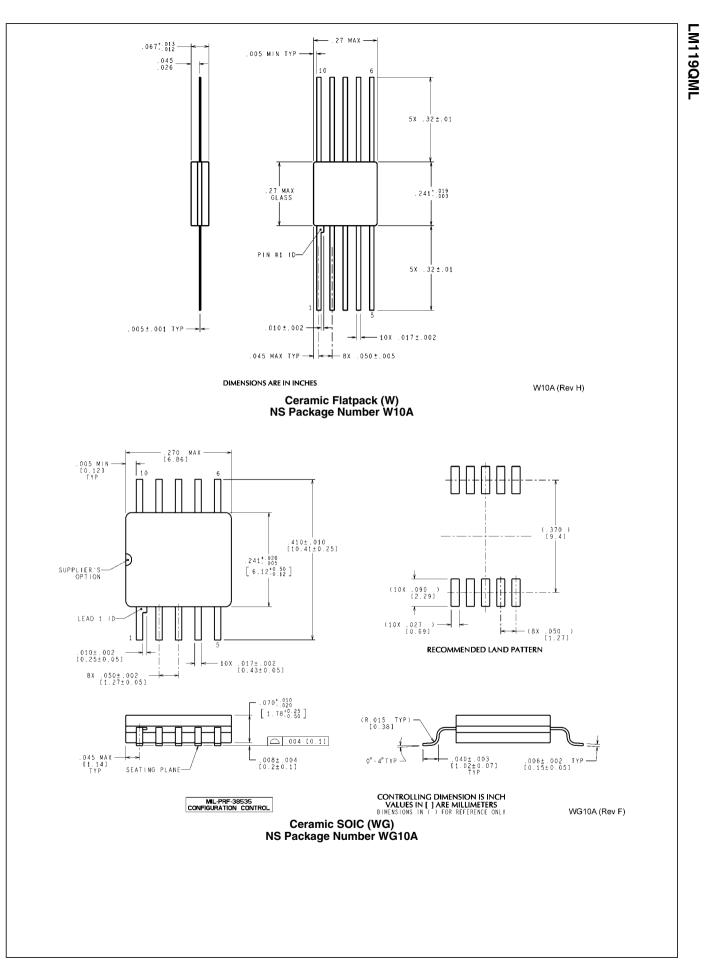
Physical Dimensions inches (millimeters) unless otherwise noted



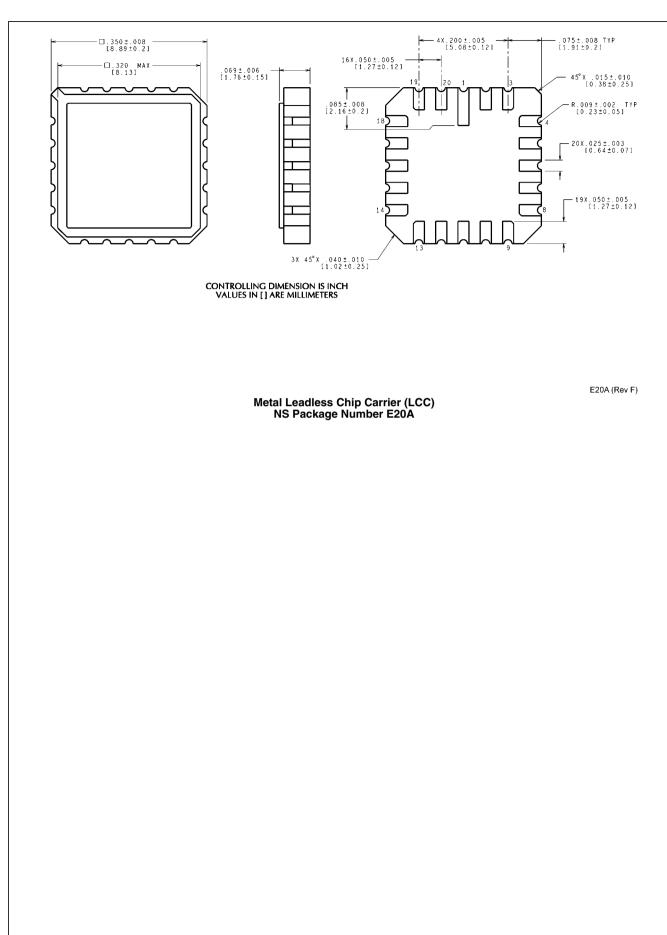
Metal Can Package (H) NS Package Number H10C



Cavity Dual-In-Line Package (J) NS Package Number J14A







Notes

Notes

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Power Management	www.national.com/power	Green Compliance	www.national.com/quality/green
Switching Regulators	www.national.com/switchers	Distributors	www.national.com/contacts
LDOs	www.national.com/ldo	Quality and Reliability	www.national.com/quality
LED Lighting	www.national.com/led	Feedback/Support	www.national.com/feedback
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